Doc No. TT4-EA-12659

Revision. 2

MOS FET

FG6943010R

## **Panasonic**

## FG6943010R

Silicon N-channel MOSFET(FET1) Silicon P-channel MOSFET(FET2)

#### For switching

#### ■ Features

- Low drive voltage: 2.5 V driveHalogen-free / RoHS compliant
  - (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol V7
- Basic Part Number FJ330301 + FK330301 (Individual)

#### ■ Packaging

Established: 2010-06-30

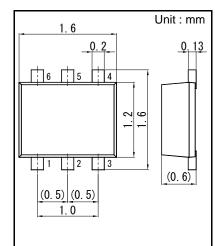
: 2013-10-10

Revised

Embossed type (Thermo-compression sealing) 8 000 pcs / reel (standard)

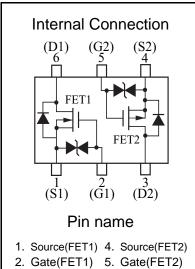
■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
FET1	Drain-source voltage	VDS	30	V	
	Gate-source voltage	VGS	±12	V	
	Drain current	ID	100	mA	
	Pulse drain current	IDp	200	mA	
FET2	Drain-source voltage	VDS	-30	V	
	Gate-source voltage	VGS	±12	V	
	Drain current	ID	-100	mA	
	Pulse drain current	IDp	-200	mA	
Overall	Total power dissipation	PT	125	mW	
	Channel temperature	Tch	150	°C	
	Operating ambient temperature	Topr	-40 to + 85	°C	
	Storage temperature	Tstg	-55 to +150	°C	
	otorago tomporataro	. 0.9	00 10 1100		



- 1. Source(FET1) 4. Source(FET2)
- 2. Gate(FET1) 5. Gate(FET2)
- 3. Drain(FET2) 6. Drain(FET1)

Panasonic	SSMini6-F3-B
JEITA	SC-107C
Code	SOT-666



3. Drain(FET2) 6. Drain(FET1)

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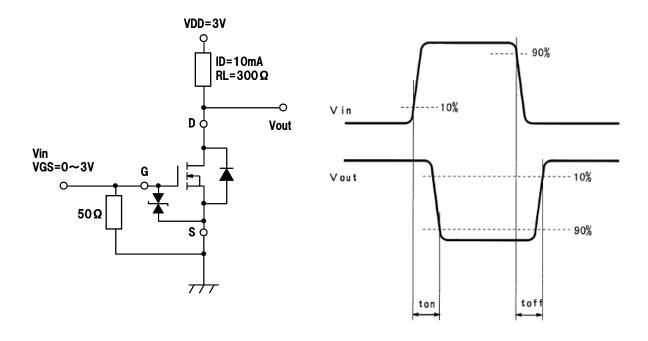
## ■ Electrical Characteristics Ta = 25 °C ± 3 °C

FET1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = 1 mA, VGS = 0	30			V
Drain-source cutoff current	IDSS	VDS = 30 V, VGS = 0			1.0	μΑ
Gate-source cutoff current	IGSS	$VGS = \pm 10 \text{ V}, VDS = 0$			±10	μΑ
Gate threshold voltage	VTH	ID = 1.0 μA, VDS = 3.0 V	0.5	1.0	1.5	V
Drain-source ON resistance	RDS(on)1	ID = 10 mA, VGS = 2.5 V		3	6	Ω
Dialii-source ON resistance	RDS(on)2	ID = 10 mA, VGS = 4.0 V		2	3	Ω
Forward transfer admittance	Yfs	ID = 10 mA, VDS = 3.0 V	20	55		mS
Input capacitance	Ciss			12		pF
Output capacitance	Coss	VDS = 3 V, $VGS = 0$ , $f = 1 MHz$		7		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on time *1	ton	VDD = 3 V, VGS = 0 to 3 V	100			nc
rurn-on time	tori	ID = 10 mA		100		ns
Turn-off time *1	toff	VDD = 3 V, VGS = 3 to 0 V		100		nc
rum-on ume	tOH	ID = 10 mA				ns

1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. \*1 FET1 Turn-on and Turn-off test circuit



Established: 2010-06-30 : 2013-10-10 Revised

## FG6943010R

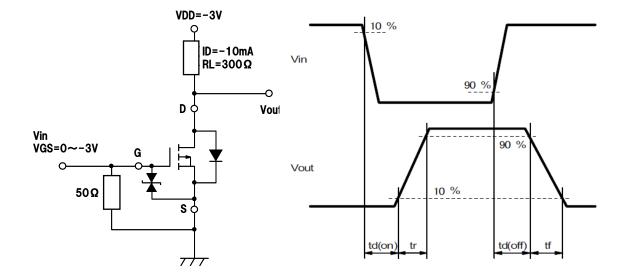
# **Panasonic**

#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C FET2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = -1mA, $VGS = 0$	-30			V
Drain-source cutoff current	IDSS	VDS = -30 V, VGS = 0			-1.0	μΑ
Gate-source cutoff current	IGSS	$VGS = \pm 10 \text{ V, VDS} = 0$			±10	μΑ
Gate threshold voltage	VTH	ID = -1.0 $\mu$ A, VDS = -3.0 V	-0.5	-1.0	-1.5	V
Drain-source ON resistance	RDS(on)1	ID = -10 mA, VGS = -2.5 V		7	17	Ω
Diani-source On resistance	RDS(on)2	ID = -10 mA, VGS = -4.0 V		4	7	Ω
Forward transfer admittance	Yfs	ID = -10 mA, VDS = -3.0 V	20	40		mS
Input capacitance	Ciss			12		pF
Output capacitance	Coss	VDS = -3 V, $VGS = 0$ , $f = 1 MHz$		7		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on time *1	ton	VDD = -3 V, VGS = 0 to -3 V,	100			ns
Turn-on time	ton	ID = -10  mA		100		113
Turn-off time *1	toff	VDD = -3 V, $VGS = -3 to 0 V$ ,		100		ns
rum-on ume	ion	ID = -10 mA				115

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. \*1 FET2 Turn-on and Turn-off test circuit

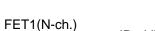


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Established: 2010-06-30 : 2013-10-10 Revised

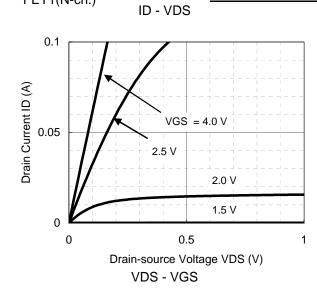
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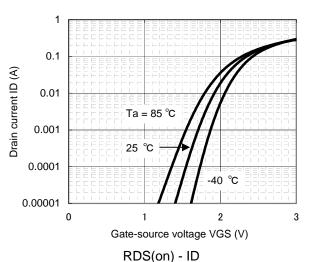
## **Panasonic**

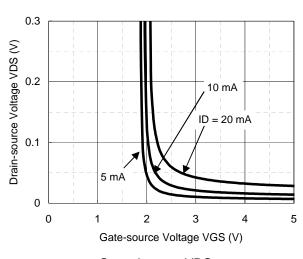


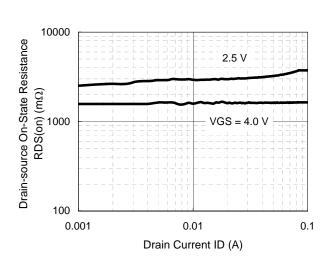
## Technical Data (reference)

ID - VGS

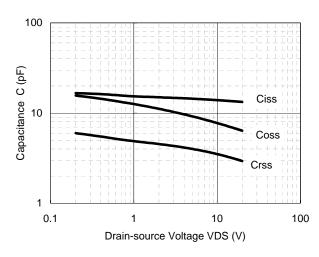








Capacitance - VDS

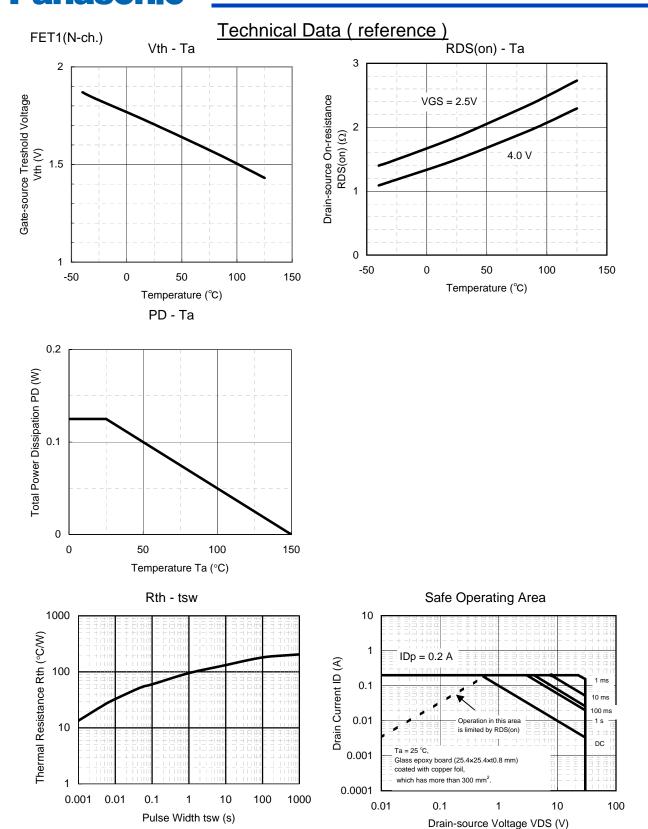


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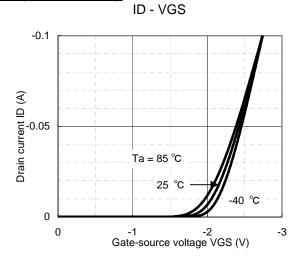


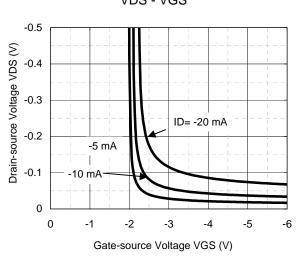
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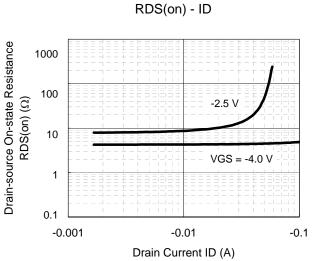
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## Technical Data (reference)

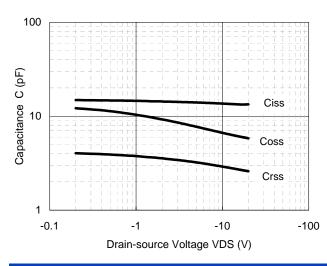
FET2(P-ch.) ID - VDS -0.1 VGS = -4.0 V Drain Current ID (A) -2.5 V -0.05 -1.5 V -2.0 V 0 0 -0.2 -0.4 -0.6 -0.8 -1 Drain-source Voltage VDS (V) **VDS - VGS** 







Capacitance - VDS

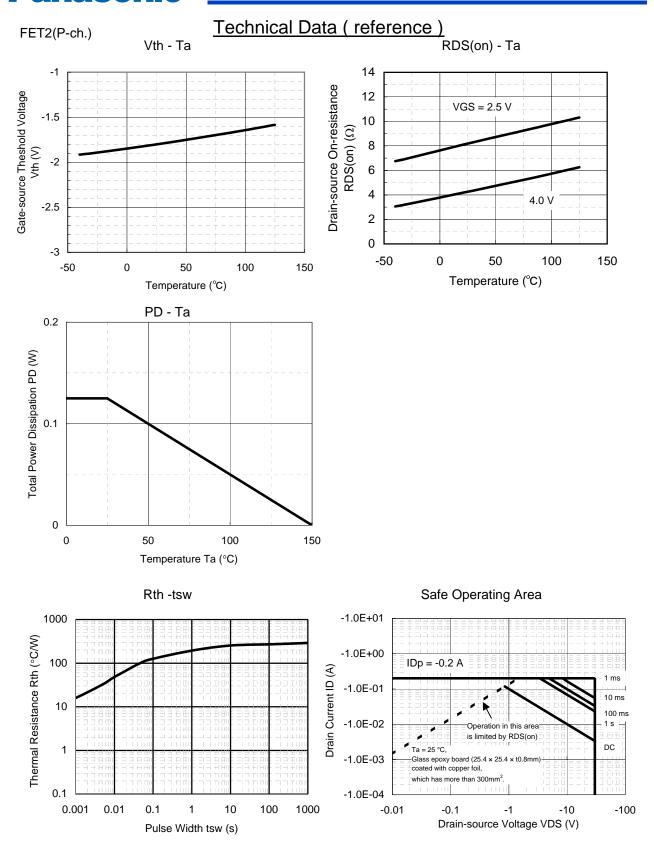


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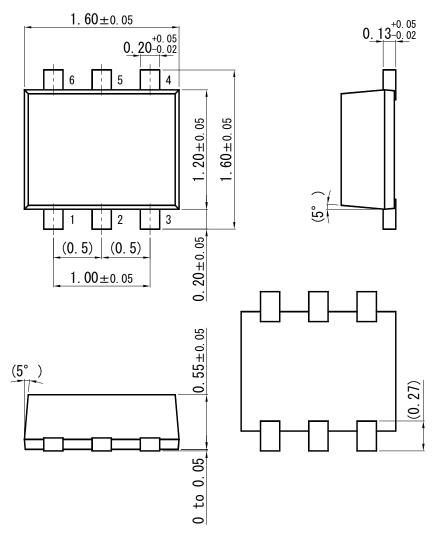


## FG6943010R

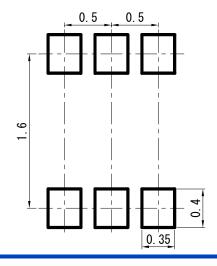
## SSMini6-F3-B

**Panasonic** 

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm



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